



Integration of rare earth ions doped Si based down converter layers in an industrial Si solar cell

Julien Cardin, L. Dumont, Christophe Labbe, P.-M. Anglade, Cédric Frilay, S.C. Wu, Ing-Song Yu, Xavier Portier, Philippe Marie, Fabrice Gourbilleau

► To cite this version:

Julien Cardin, L. Dumont, Christophe Labbe, P.-M. Anglade, Cédric Frilay, et al.. Integration of rare earth ions doped Si based down converter layers in an industrial Si solar cell. E-MRS fall meeting 2019, Sep 2019, Varsovie, Poland. hal-02301126

HAL Id: hal-02301126

<https://normandie-univ.hal.science/hal-02301126>

Submitted on 30 Sep 2019

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

Integration of rare earth ions doped Si based down converter layers in an industrial Si solar cell

J. Cardin(1), L. Dumont(1), C. Labbé(1), P.-M. Anglade(1), C. Frilay(1), S.C. Wu(2), I.-S. Yu(2), X. Portier(1), P. Marie(1), F. Gourbilleau(1).

(1) CIMAP, Normandie Univ, ENSICAEN, UNICAEN, CEA, CNRS, 14000 Caen, France

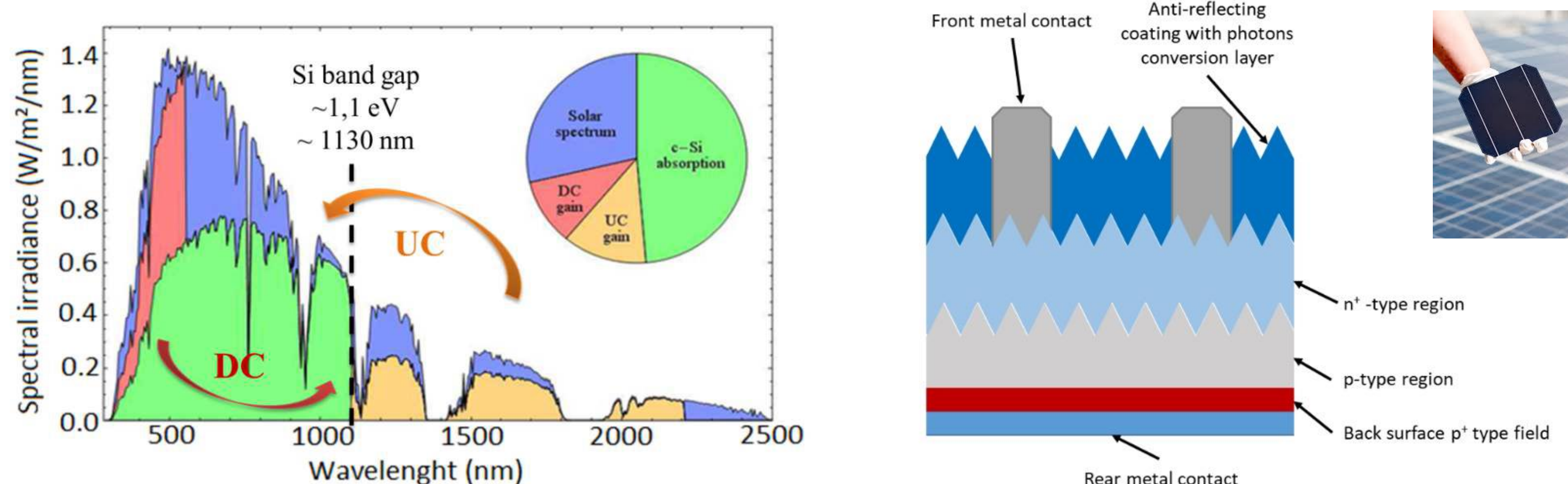
Email : julien.cardin@ensicaen.fr

(2) Department of Materials Science and Engineering, National Dong Hwa University, Hualien, Taiwan

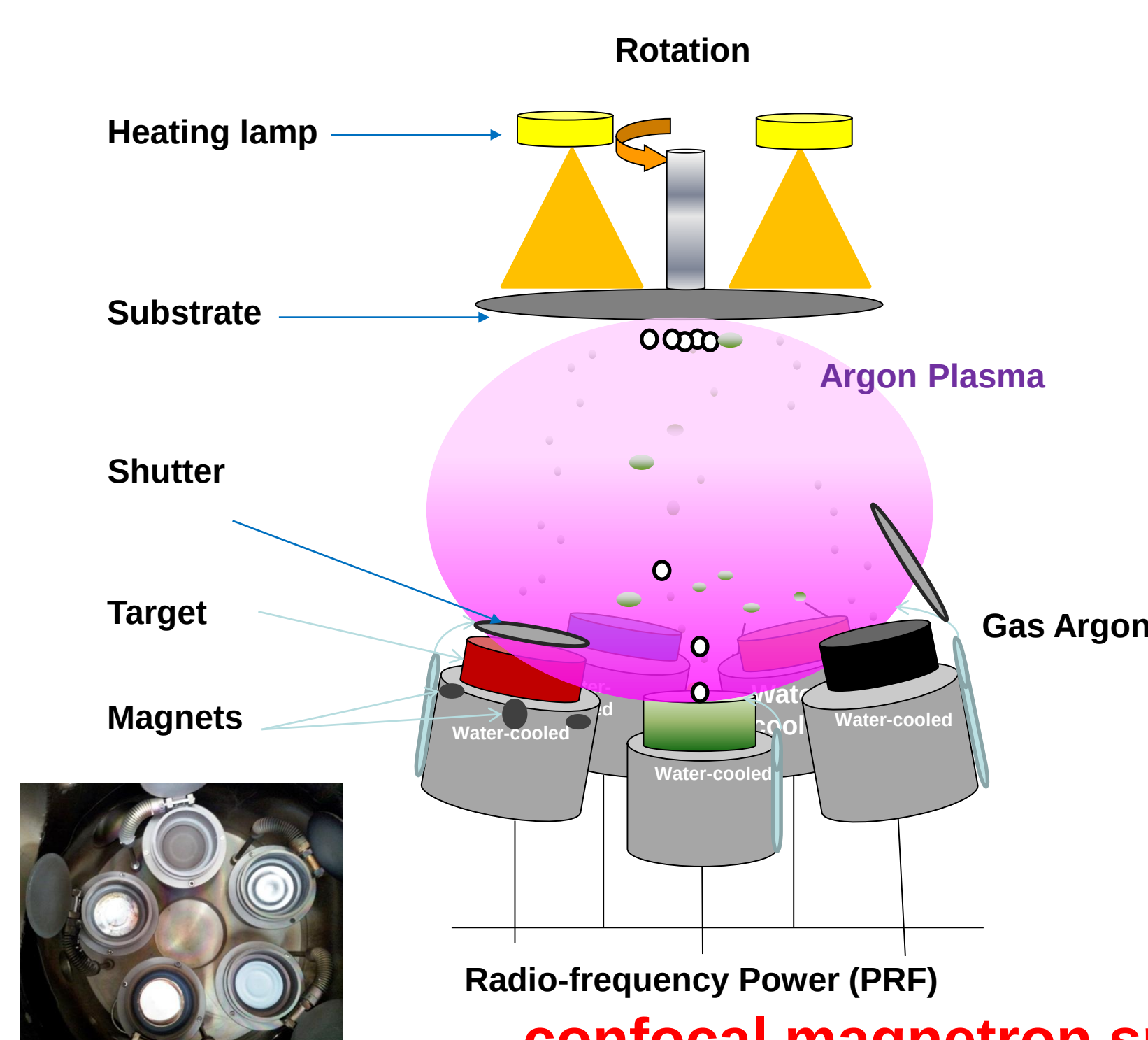
Introduction

Goal : Improve the efficiency of Si solar cells by down converter layer

- Decrease the thermalization losses due to the spectral mismatch between the solar irradiance and the Si absorption
- Use the optical properties of **rare earth ions** embedded in a Si-based matrix to do **Down-conversion (DC)**

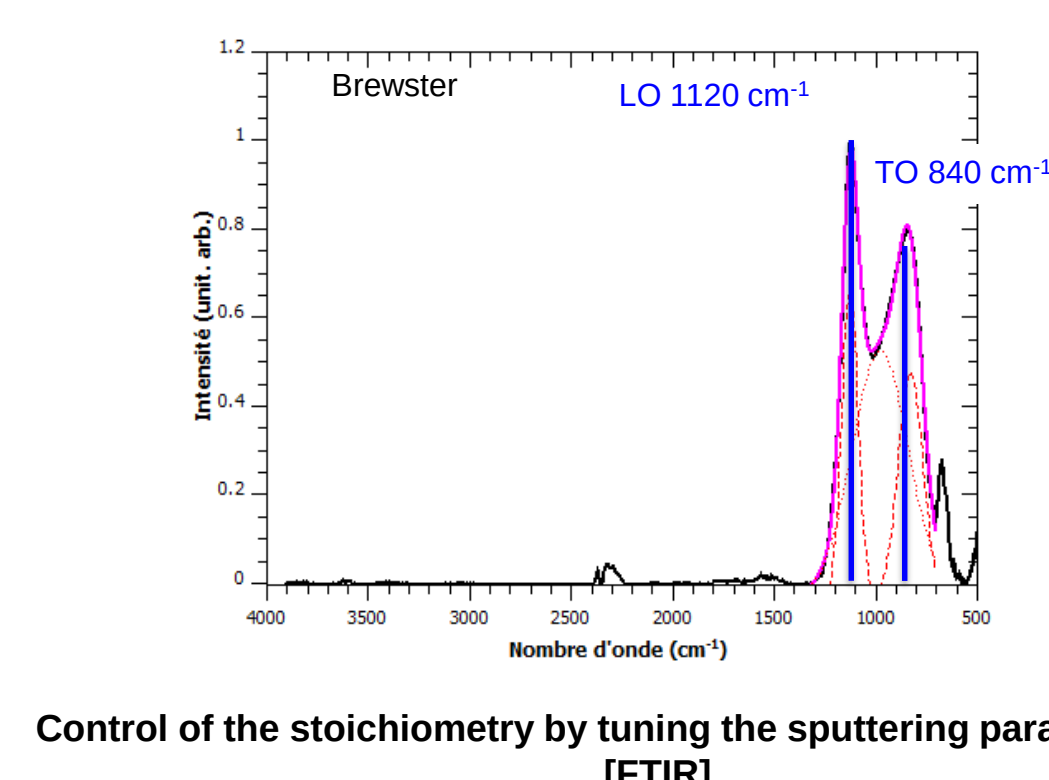


Sample fabrication

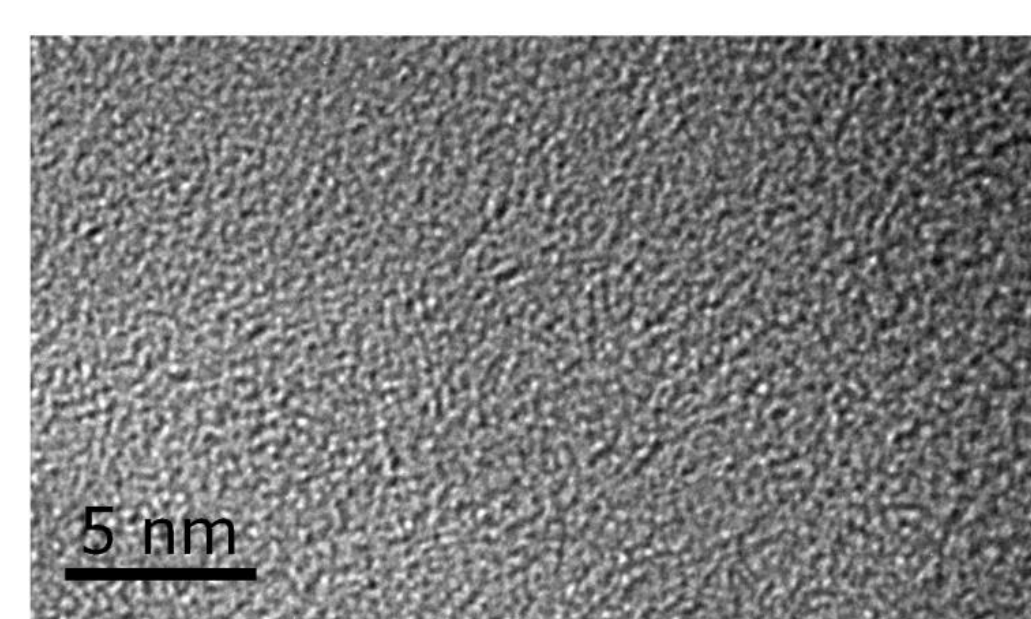


Fabrication parameters:

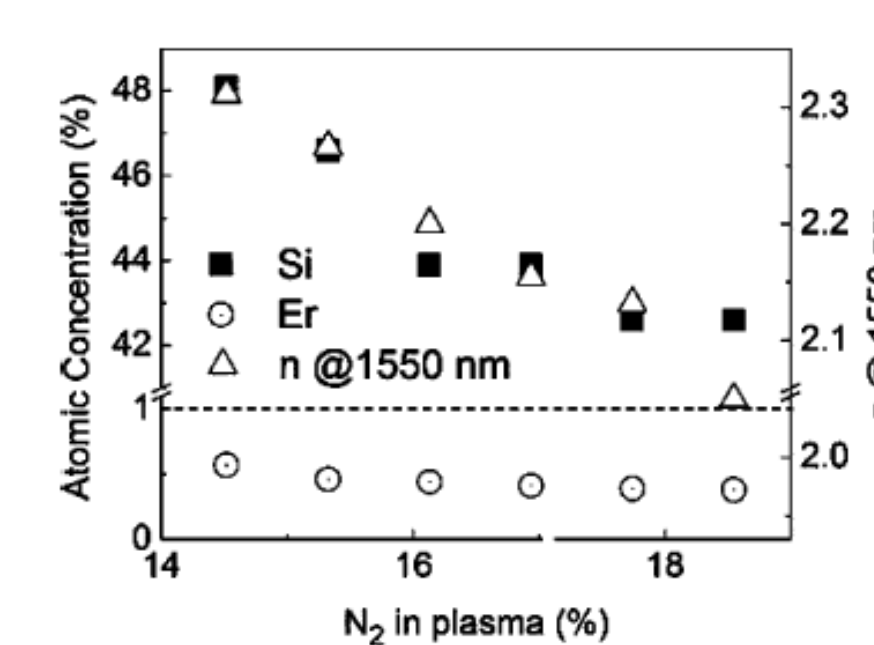
Depositions parameters:
 Deposition Temperature, T_{dp} (°C)
 Plasma Pressure, P_{tot} (sccm)
 Gaz : Argon and nitrogen
 Nitrogen rate, r_{N_2}
 RF Power density on target, P_{target} (W/cm²)
 Depositing time, t_{dp} (s)
 Annealing with rapid or slow ramp of T under specific gas (N₂, Forming...)



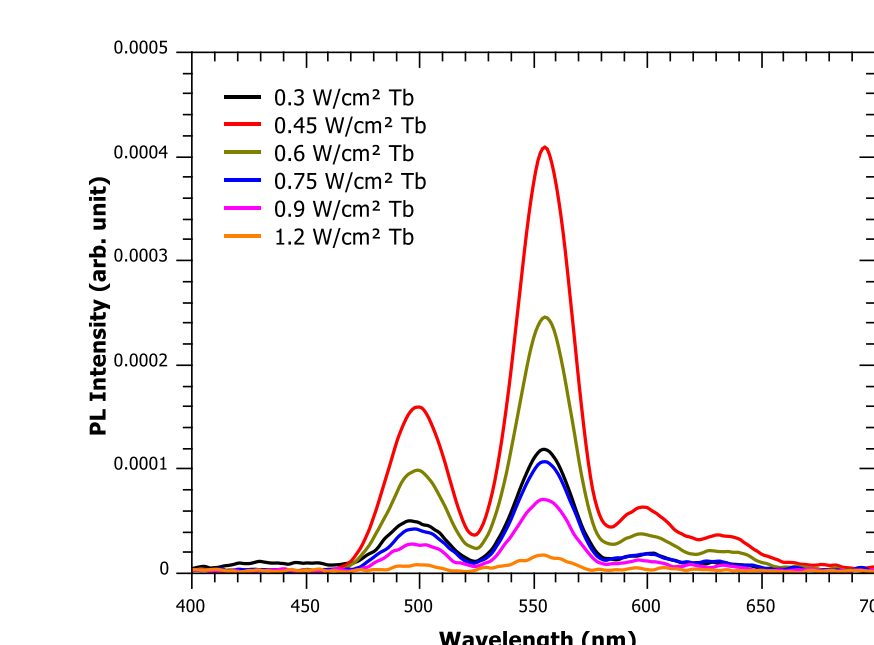
Control of the stoichiometry by tuning the sputtering parameters: SiN_x [FTIR]



Amorphous and homogenous films: SiN_x [HRTEM]



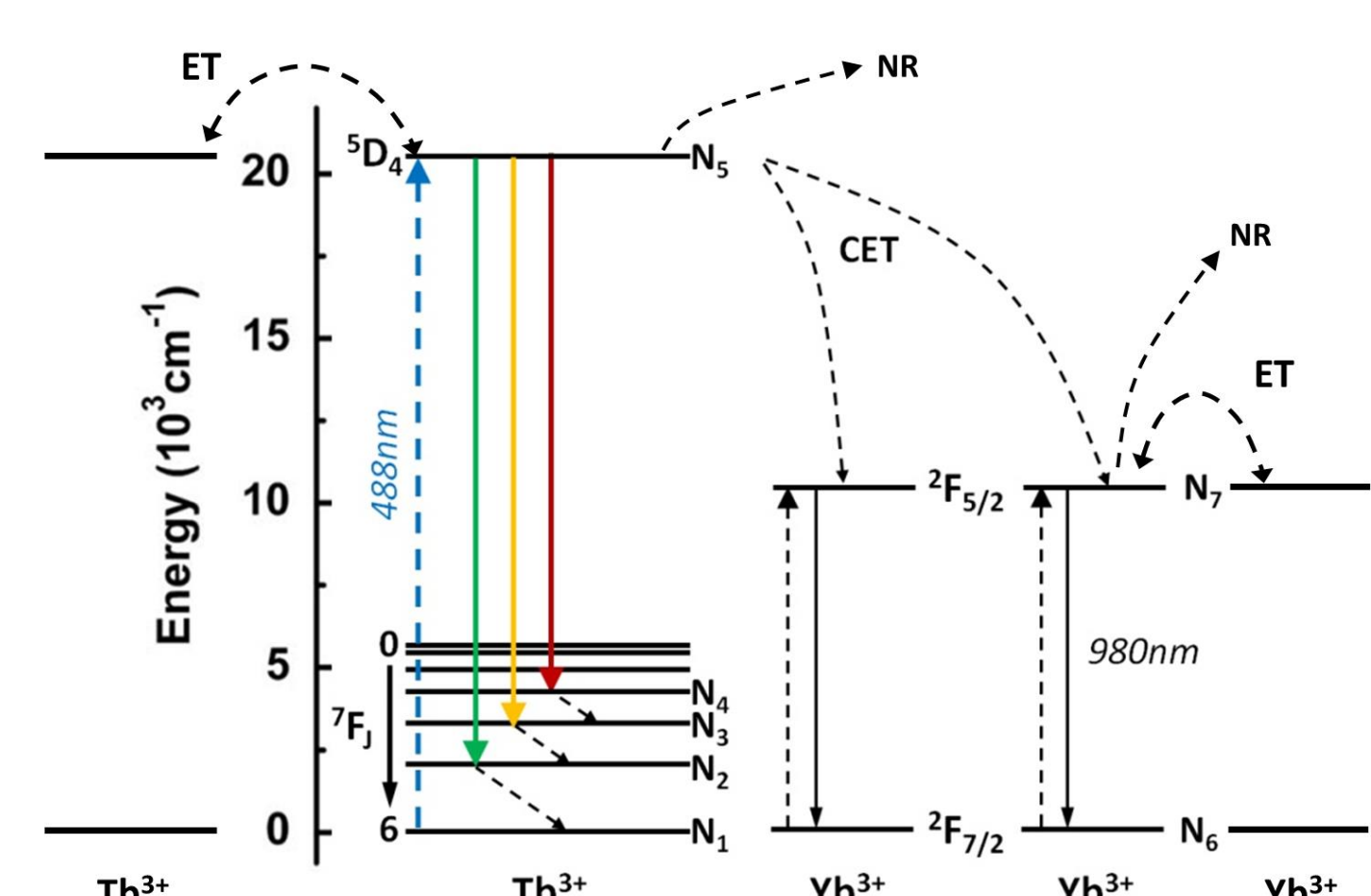
Control of refractive index by tuning the sputtering parameters : SiN_x [ELLIPSOMETRY]



Si based doped with rare earth ions luminescent layer: SiN_x-Tb³⁺ [PHOTOLUMINESCENCE]

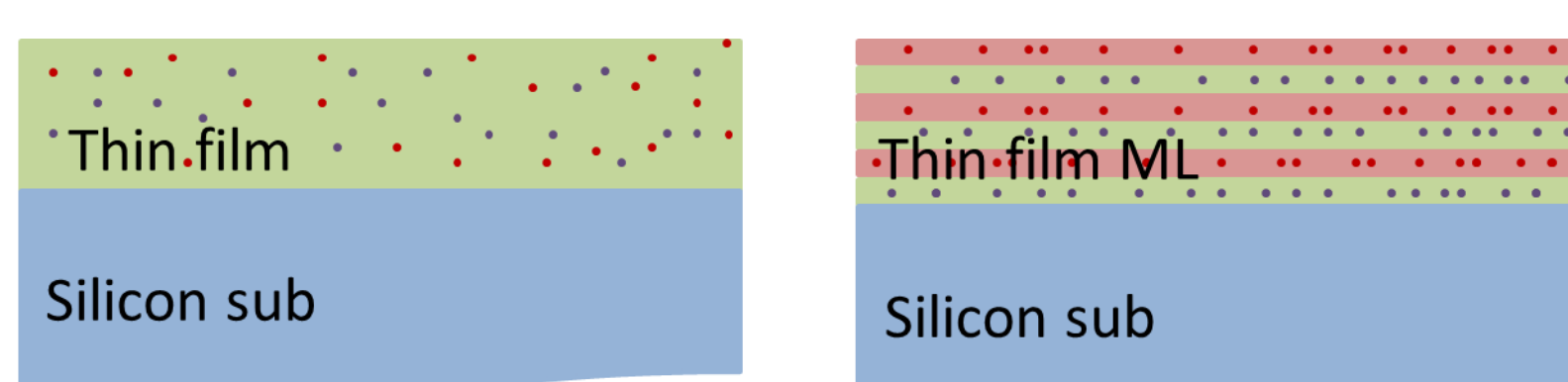
Structural and physical characterization

Monte Carlo Modeling

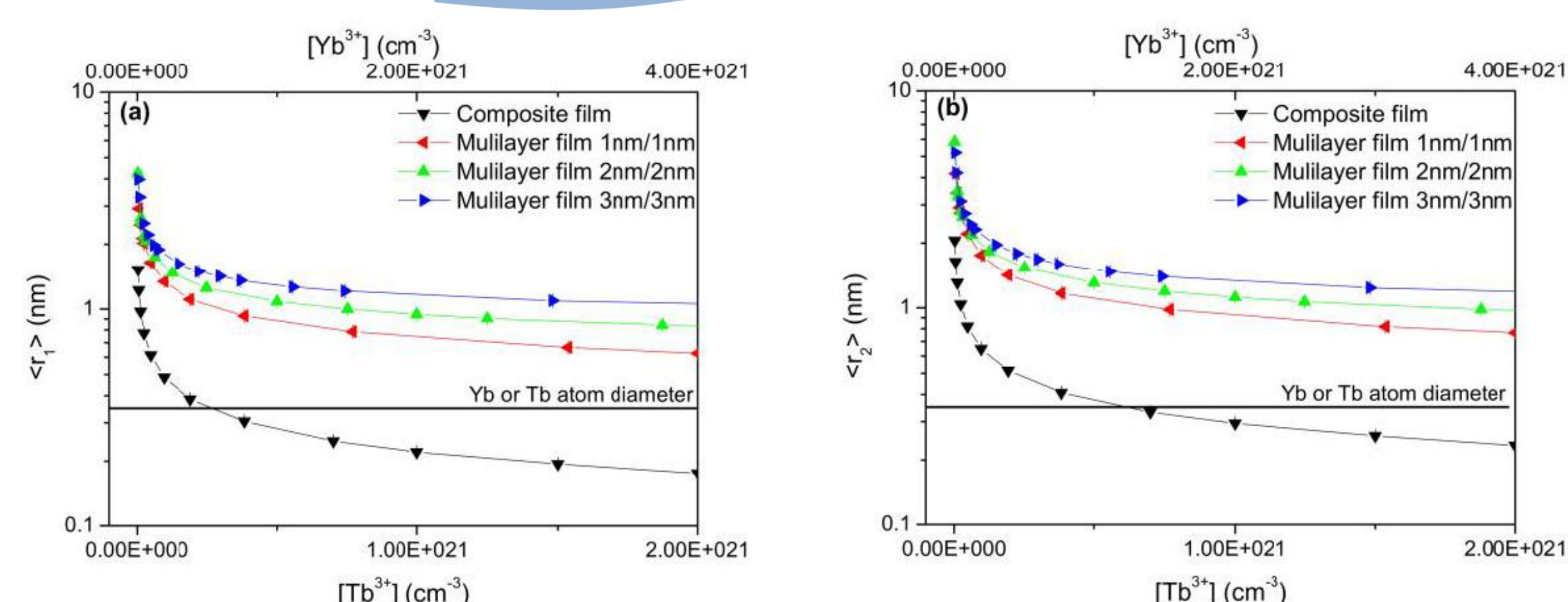


K_{CET} distance dependent and therefore function of concentration [Tb³⁺] and [Yb³⁺] and their distribution

$$K_{CET} \propto \frac{1}{r_{Tb^{3+}-Yb^{3+}}^6 \cdot r_{Tb^{3+}-Yb^{3+}}'^6}$$

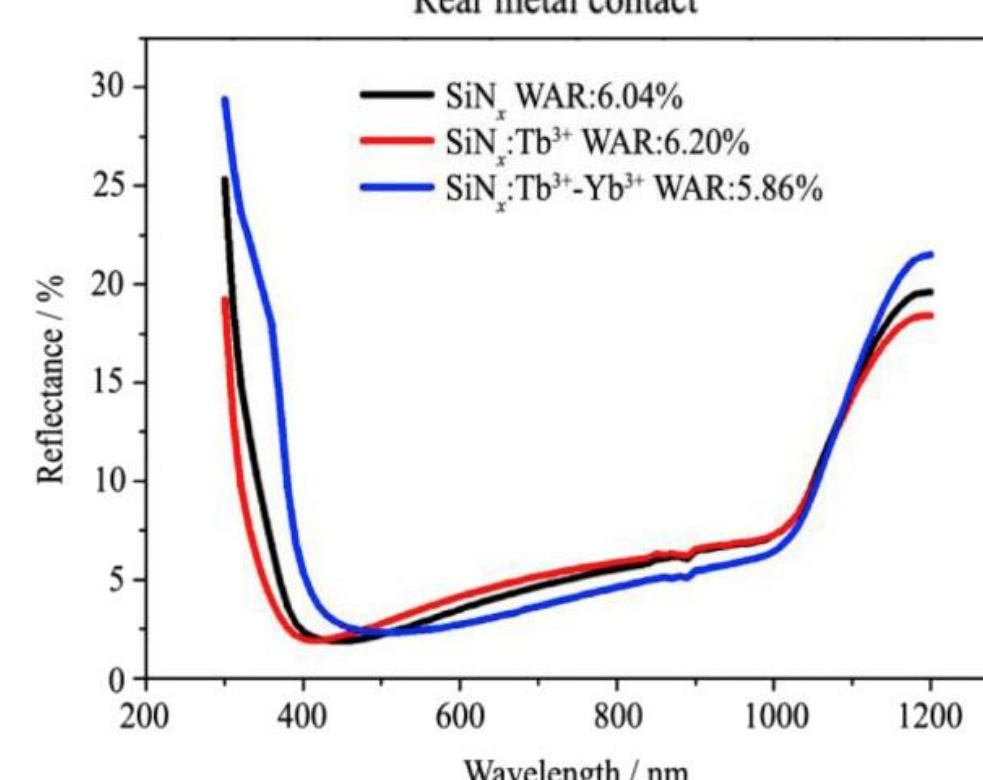
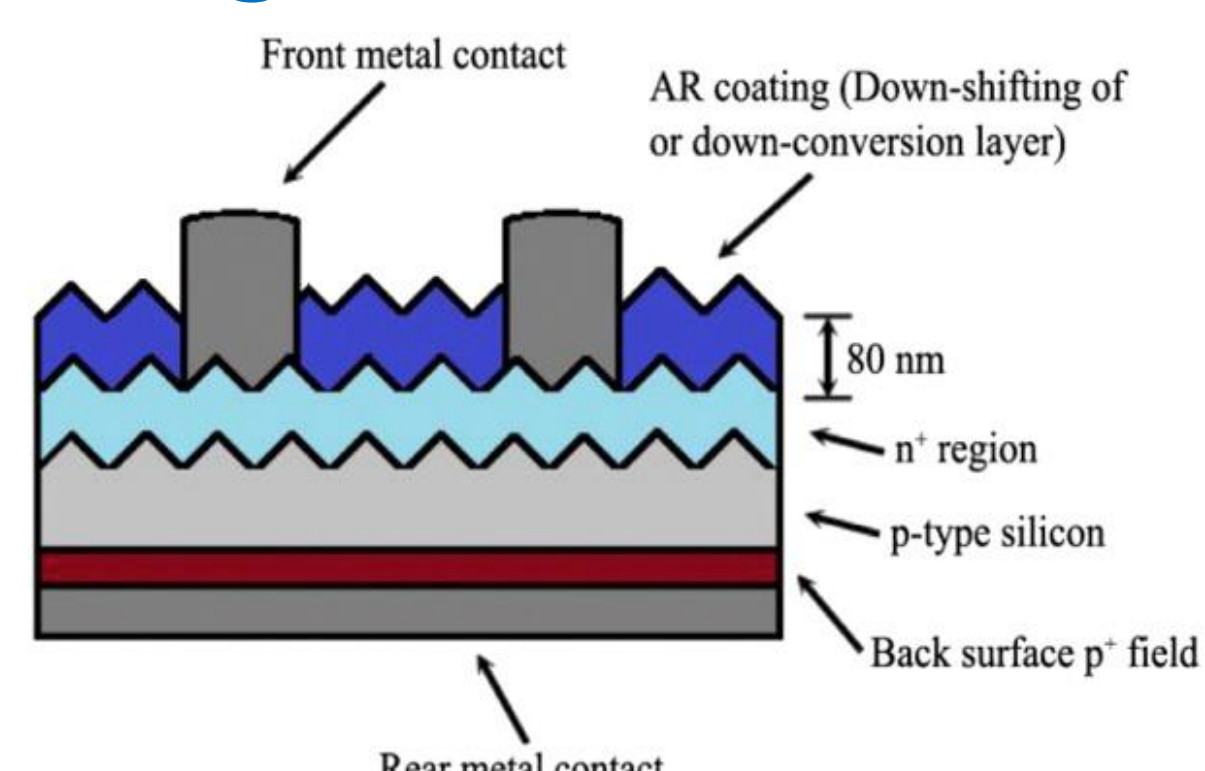


Two kinds of Tb³⁺-Yb³⁺ co-doped thin films fabricated homogenous and multilayer

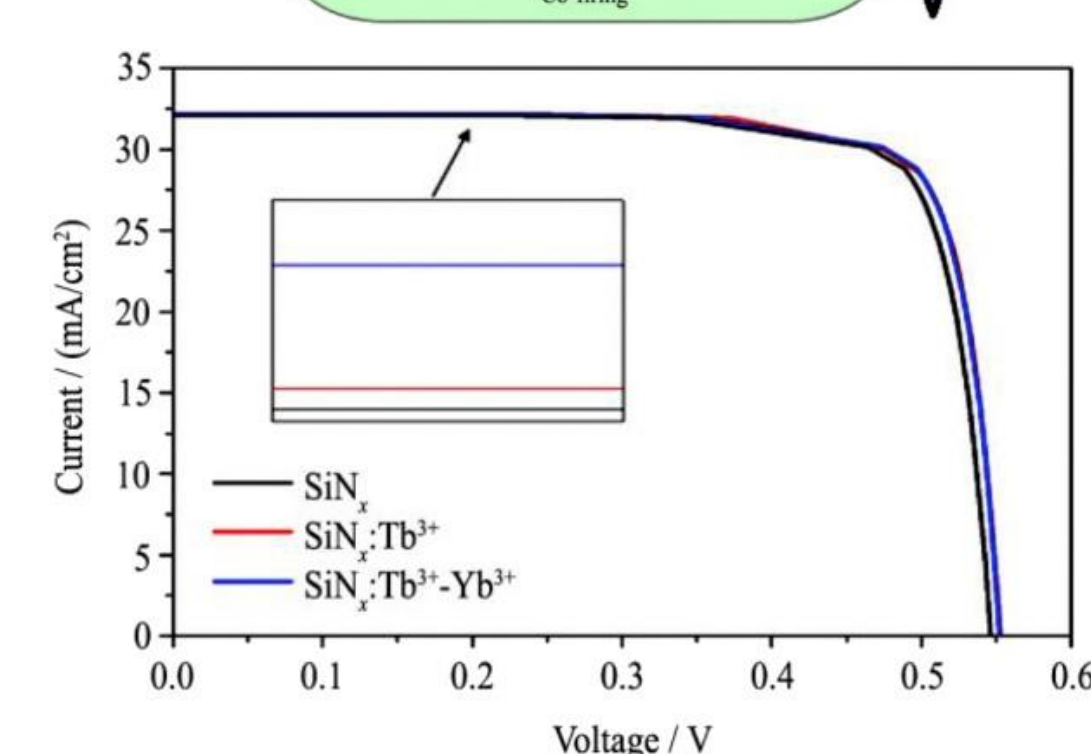
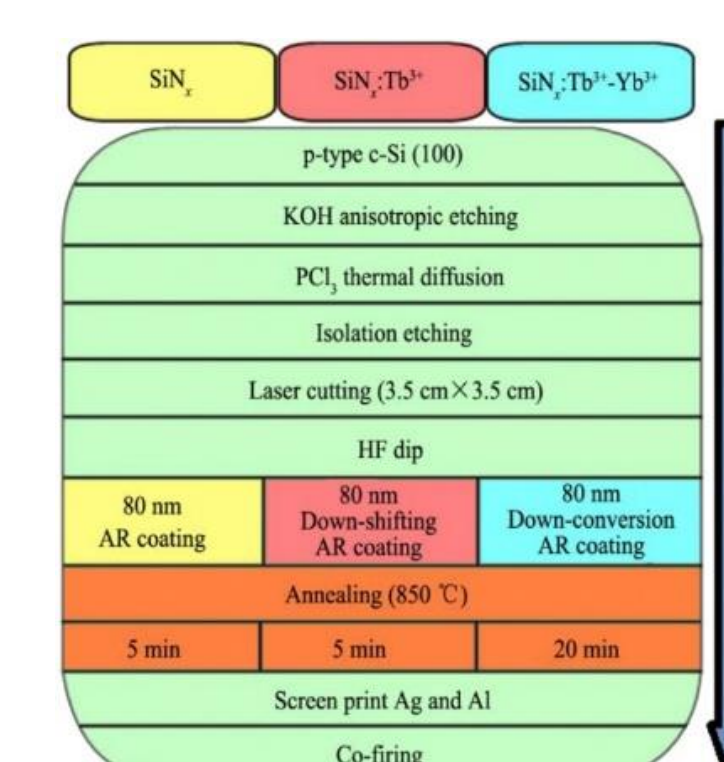


Multilayer prevent aggregation quenching and allow therefore higher doping rate

Integration in industrial Si solar cell



Reflectance of three layers deposited on textured emitters



Pseudo I-V curves for three c-Si solar cells with SiN_x, SiN_x:Tb³⁺ and SiN_x:Tb³⁺-Yb³⁺ layers, respectively.

Samples	J_{sc} (mA/cm ²)	V_{oc} (V)	Pseudo FF (%)	Pseudo Efficiency (%)	Efficiency to normalized transmission (%)
SiN _x	32.091	0.546	0.804	17.13	18.23
SiN _x :Tb³⁺	32.098	0.552	0.803	17.31	18.45
SiN _x :Tb³⁺-Yb³⁺	32.165	0.552	0.806	17.36	18.44

Relative increase by 1.34% in the solar cell conversion efficiency

Conclusion

- Fabrication of Tb/Yb-doped SiN_x homogenous and multilayer films ->DC optimized films
- Modeling of the DC interaction exchange for both kind of films -> Aggregation of rare earth ions is prevented in multilayer
- Homogenous and multilayer DC layers integrated in Si solar cell -> Homogenous DC layer lead to relative Si solar cell efficiency increase of 1.34%